DRIVER FOR IGBT MODULES

#### DESCRIPTION

VLA500-01R is a hybrid integrated circuit designed for driving n-channel IGBT modules in any gate-amplifier application. This device include the isolated type DC-DC converter for a Gate drive. Therefore design of the gate power supply is not required.

The system of built-in short circuit protection provide a margin to time by function to maintain reverse bias for a predetermined time after the detection of short circuit.

Recommended IGBT modules:

 $V_{CES}$ =600V series up to 600A class  $V_{CES}$ =1200V series up to 1400A class

#### FEATURES

•Built-in the isolated type DC-DC converter for gate drive •SIP outline allows more space on mounting area •Built-in short circuit protection (With fault output)

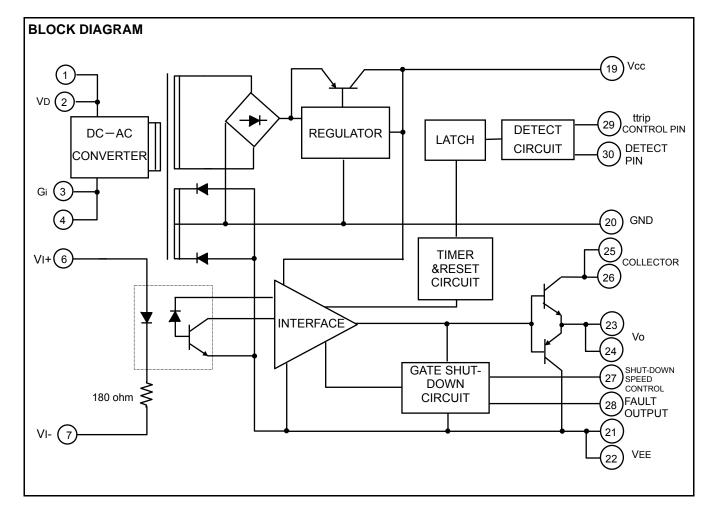
·Variable fall time on activity of short circuit protection

•Electrical isolation voltage between input and output is 2500Vrms (for 1minute)

•TTL compatible input.

### **APPLICATIONS**

To drive IGBT modules for inverter or AC servo systems application



HYBRID IC

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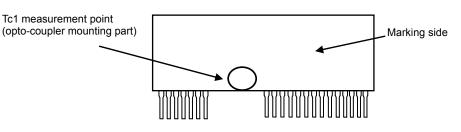
Symbol	Parameter	Conditions	Ratings	Unit
VD	Supply voltage	DC	-1~16.5	V
VI	Input signal voltage	Applied between pin 6 – 7 50% duty cycle, pulse width 1ms	-1 ~ +7	
Vo	Output voltage	When the output voltage is "H"	V <sub>CC</sub>	V
I <sub>OHP</sub>	Output current	Pulse width 2µs	-12	Α
I <sub>OLP</sub>		Fuise width zps	12	Α
Viso	Isolation voltage	Sine wave voltage 60Hz, for 1min.	2500	Vrm
T <sub>C</sub> 1	Case temperature1	Surface temperature(opto-coupler mounting part) (*3)	85	°C
T <sub>C</sub> 2	Case temperature2	Surface temperature(excepting opto-coupler mounting part)	100	°C
Topr	Operating temperature	No condensation allowable	-20 ~ +60	°C
Tstg	Storage temperature	No condensation allowable	-25 ~ +100 (*1)	°C
I <sub>FO</sub>	Fault output current	Applied pin 28	20	mA
V <sub>R30</sub>	Input voltage to pin 30	Applied pin 30	50	V
I <sub>drive</sub>	Gate drive current	Gate average current	210 (*2)	mA

#### MAXIMUM RATINGS (Unless otherwise noted, Ta=25°C)

(\*1) Differs from H/C condition

(\*2) Refer to Idrive-Ta CHARACTERISTICS (Needs derating)

(\*3) Refer to the below figure.



#### ELECTRICAL CHARACTERISTICS (Unless otherwise noted, Ta=25°C, VD=15V, RG=2.2 ohm)

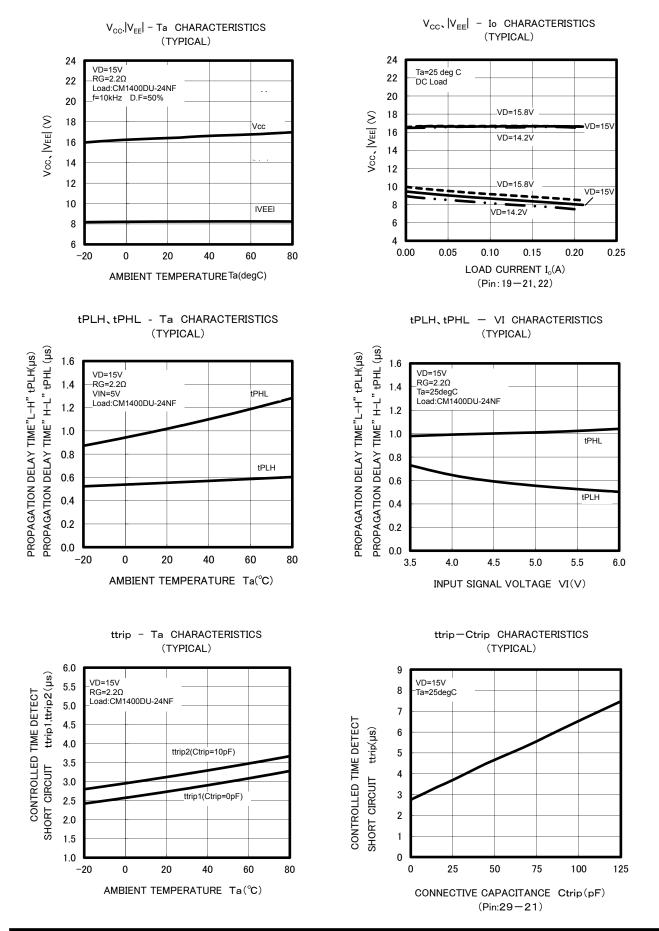
Symbol	Parameter	Conditions	Limits			Unit
Symbol	Falameter	Conditions		Тур	Max	Unit
VD	Supply voltage	Recommended range	14.2	15	15.8	V
V <sub>IN</sub>	Pull-up voltage on input side	Recommended range		5	5.25	V
I <sub>IH</sub>	"H" input current	Recommended range	15.2	16	19	mA
f	Switching frequency	Recommended range	-	-	20	kHz
$R_{G}$	Gate resistance	Recommended range	1	-	-	ohm
IIH	"H" input current	V <sub>IN</sub> = 5V	-	16	-	mA
Vcc	Gate positive supply voltage		15.2	-	17.5	V
VEE	Gate negative supply voltage		-6	-	-11.5	V
Eta	Gate supply efficiency	Load current = 210mA Eta = (Vcc+IVEE I) x 0.21 / (15 x ID) x 100	60	75	-	%
V <sub>OH</sub>	"H" output voltage	10k ohm connected between pin 23-20	14	15.3	16.5	V
V <sub>OL</sub>	"L" output voltage	10k ohm connected between pin 23-20	-5.5	-	-11	V
t <sub>PLH</sub>	"L-H" propagation time	I <sub>IH</sub> = 16mA	0.3	0.6	1	μs
t <sub>r</sub>	"L-H" rise time	I <sub>IH</sub> = 16mA	-	0.3	1	μs
t <sub>PHL</sub>	"H-L" propagation time	I <sub>IH</sub> = 16mA	0.6	1	1.3	μs
t <sub>f</sub>	"H-L" fall time	I <sub>IH</sub> = 16mA	-	0.3	1	μs
t <sub>timer</sub>	Timer	Between start and cancel (under input sign "L")	1	-	2	ms
I <sub>FO</sub>	Fault output current	Applied pin 28, R = 4.7k ohm	-	5	-	mA
t <sub>trip1</sub>	Controlled time detect short circuit 1	Pin 30 : 15V and more, pin 29 : open	-	2.8	-	μs
t <sub>trip2</sub>	Controlled time detect short circuit 2 (*4)	Pin 30 : 15V and more, pin 29-21,22 : 10pF (connective capacitance)	-	3.2	-	μs
V <sub>SC</sub>	SC detect voltage	Collector voltage of module	15	-	-	V

(\*4) Length of wiring of condenser controlled time detect short-circuit is within 5cm from pin 21,22 and 29 coming and going.

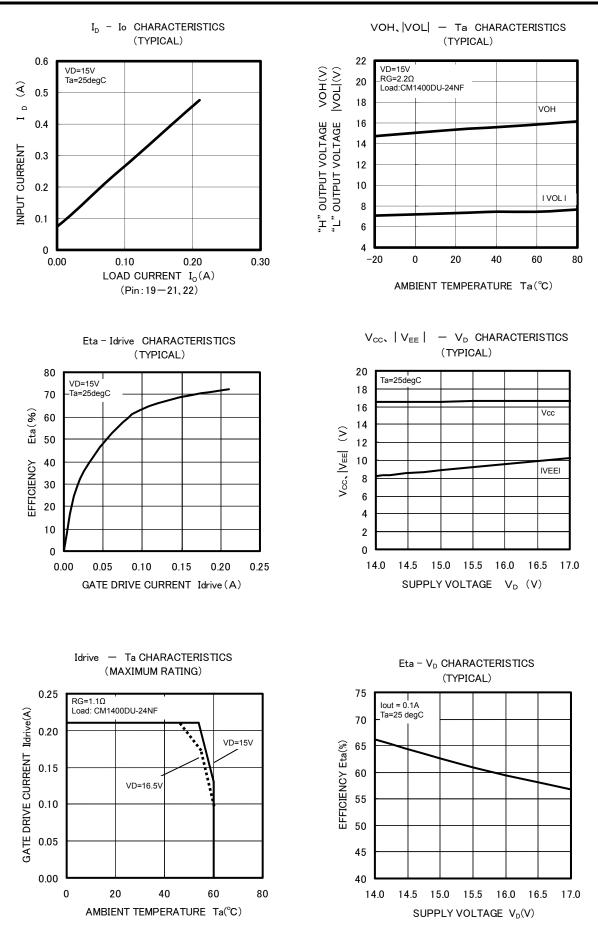


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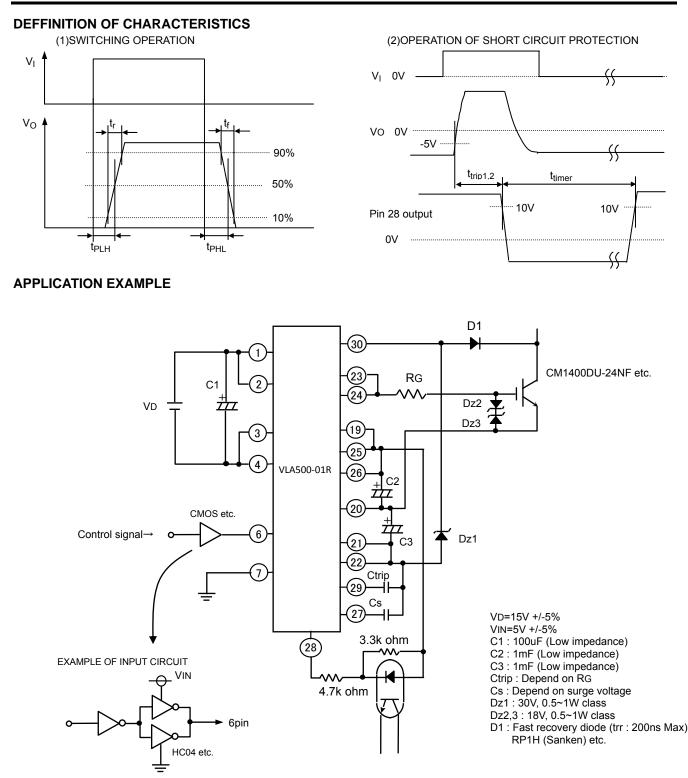
#### PERFORMANCE CURVES



#### DRIVER FOR IGBT MODULES



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#### PRECAUTION

- (1) Voltage compensate capacitors are expected to be located as close as possible to the Hybrid IC.
- (2) Minimize the area of closed circuit of gate circuit so as not to be affected by induction noise.
- (3) D1 requires approximately the same voltage of power modules.
- (4) When recovery current flow in D1, pin 30 is applied high voltage.In that case, counterplan for protection which insert a zener diode between pin 21,22 and 30 are necessary like above diagram.
- (5) When the built in short-circuit protection circuit is not necessary to be used, please connect resistor of 4.7k ohm between pin 30 and 20. (D1 and Dz1 are not required.)



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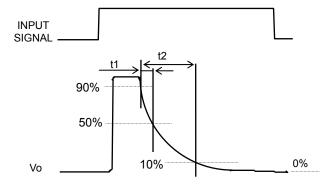
#### **OPERATION OF PROTECTION CIRCUIT**

- (1) In case the gate voltage is "H" and the collector voltage is high, this Hybrid IC will recognize the circuit as short circuit and immediately reduce the gate voltage. Besides, put out a fault sign ("L") which inform that protection circuit is operating at the same time from pin 28.
- (2) The protection circuit reset and resorted to ordinary condition if input sign is "L" when the predetermined time(1 ~ 2ms) passed.
   ("L" period needs 15us or more )
- When the output rises, the controlled time detect short circuit (Typ 2.8us) is set up so that on-time of IGBT can be secured properly. It is possible to adjust that time by connecting the capacitor (Ctrip) between pin 21,22 and 29.

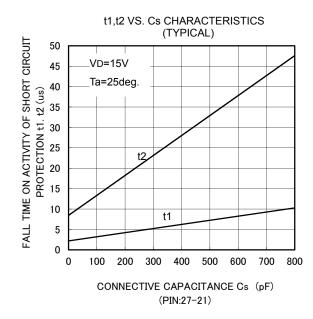
### ADJUSTMENT OF OUTPUT FALL TIME

#### (When the protection circuit is operating)

In case you want to decrease the speed of reverse bias when the protection circuit is operating, you can adjust that speed by connecting the capacitor (Cs) between pin 21,22 and 27. (Please refer to under figures.)



# START DETECTION OF SHORT CIRCUIT GATE SHUTDOWN CIRCUIT OPERATE TIMER START OUTPUT FAULT SIGN END OF TIMER YES RESET



Note : "L" output voltage with protection circuit operating is about VEE + 2V.



### **OPERATION FLOW ON DETECTING SHORT CIRCUIT**

## HYBRID IC

DRIVER FOR IGBT MODULES

### CAPACITY FOR POWER SUPPLY ON INPUT SIDE

This product has isolated DCDC converter built in for gate drive.

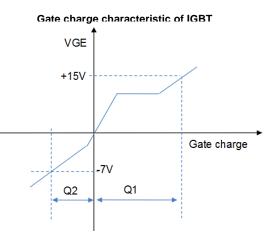
When you chose the power supply on input side,

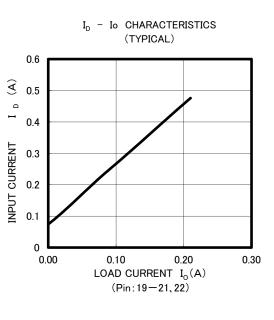
please select the product that can supply the current capacity proven by next 3steps.

1st step : Calculation for gate average current

Idrive = (Q1+IQ2I) X f Idrive : Gate average current Q1 : Gate charge at +15V (Read from data sheet of IGBT) Q2 : Gate charge at -7V (Read from data sheet of IGBT)

f : Switching frequency of IGBT





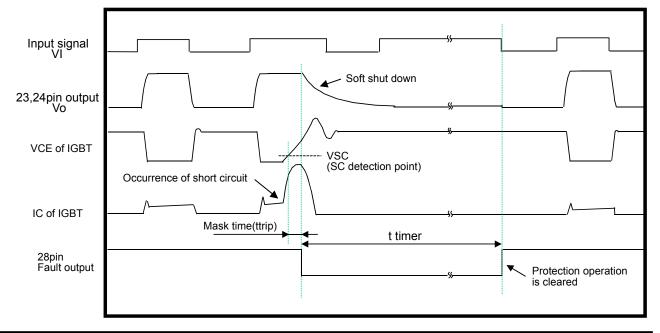
2nd step : Reading required current from performance curve

If the result of calculation for Idrive is 100mA ID is about 270mA by right chart. ID : Consumption current of DCDC converter in this HIC

3rd step : Securing the margin

Iout = ID x (1+ margin ) Iout : Output current of input power supply Margin : 0.4

If the result of ID is 270mA, please prepare the power supply that has the following spec. Output voltage : 15V Output current : more than378mA



#### TIMING CHART

# HYBRID IC

#### FOR SAFETY USING

Great detail and careful attention are given to the production activity of Hics, such as the development, the quality of production, and in it's reliability. However the reliability of Hics depends not only on their own factors but also in their condition of usage. When handling Hics, please note the following cautions.

	CAUTIONS			
Packing	The materials used in packing Hics can only withstand normal external conditions. When exposed to outside shocks, rain and certain environmental contaminators, the packing mater will deteriorates. Please take care in handling.			
Carrying	<ol> <li>Don't stack boxes too high. Avoid placing heavy materials on boxes.</li> <li>Boxes must be positioned correctly during transportation to avoid breakage.</li> <li>Don't throw or drop boxes.</li> <li>Keep boxes dry. Avoid rain or snow.</li> <li>Minimal vibration and shock during transportation is desirable.</li> </ol>			
Storage	<ul> <li>When storing Hics, please observe the following notices or possible deterioration of their electrical characteristics, risk of solder ability, and external damage may occur.</li> <li>1) Devices must be stored where fluctuation of temperature and humidity is minimal, and must not be exposed to direct sunlight. Store at the normal temperature of 5 to 30 degrees Celsius with humidity at 40 to 60%.</li> <li>2) Avoid locations where corrosive gasses are generated or where much dust accumulates.</li> <li>3) Storage cases must be static proof.</li> <li>4) Avoid putting weight on boxes.</li> </ul>			
Extended storage	When extended storage is necessary, Hics must be kept non-processed. When using Hics which have been stored for more than one year or under severe conditions, be sure to check that the exterior is free from flaw and other damages.			
Maximum ratings	To prevent any electrical damages, use Hics within the maximum ratings. The temperature, current, voltage, etc. must not exceed these conditions.			
Polarity	To protect Hics from destruction and deterioration due to wrong insertion, make sure of polarity in inserting leads into the board holes, conforming to the external view for the terminal arrangement.			





## ISAHAYA ELECTRONICS CORPORATION

Marketing division, Marketing planning department

6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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